



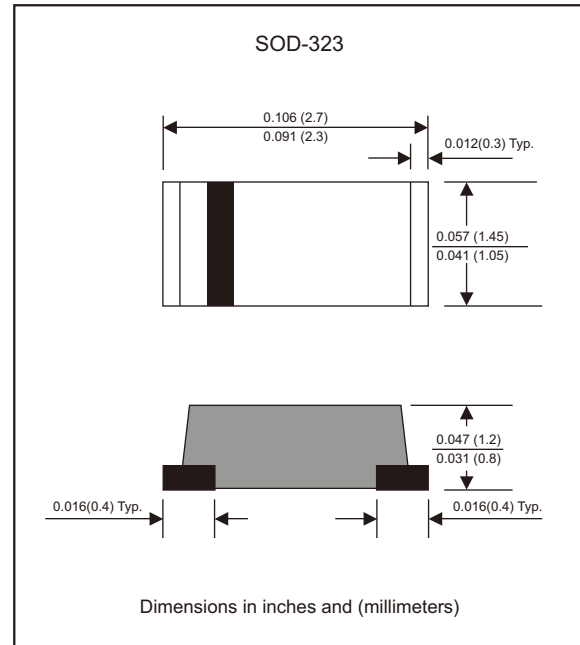
Package outline

Features

- Batch process design, excellent power dissipation offers better reverse leakage current and thermal resistance.
- Low profile surface mounted application in order to optimize board space.
- Low power loss, high efficiency.
- High current capability, very low forward voltage drop.
- High surge capability.
- Guardring for overvoltage protection.
- Very tiny plastic SMD package.
- Ultra high-speed switching.
- Silicon epitaxial planar chip, metal silicon junction.
- Lead-free parts meet environmental standards of MIL-STD-19500 /228

Mechanical data

- Epoxy : UL94-V0 rated flame retardant
- Case : Molded plastic, SOD-323
- Terminals :Plated terminals, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.008 gram



Maximum ratings (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	See Fig.2	I_O			1.0	A
Forward surge current	8.3ms single half sine-wave superimposed on rate load (JEDEC methode)	I_{FSM}			30	A
Reverse current	$V_R = V_{RRM}$ $T_J = 25^{\circ}\text{C}$	I_R			0.5	mA
Thermal resistance	Junction to ambient	$R_{\theta JA}$		90		$^{\circ}\text{C/W}$
Diode junction capacitance	$f=1\text{MHz}$ and applied 4V DC reverse voltage	C_J		130		pF
Storage temperature		T_{STG}	-65		+175	$^{\circ}\text{C}$

SYMBOLS	V_{RRM}^{*1} (V)	V_{RMS}^{*2} (V)	V_R^{*3} (V)	V_F^{*4} (V)	Operating temperature T_U ($^{\circ}\text{C}$)
SL12N	20	14	20	0.38	-55 to +100
SL13N	30	21	30	0.40	
SL14N	40	28	40	0.40	

*1 Repetitive peak reverse voltage

*2 RMS voltage

*3 Continuous reverse voltage

*4 Maximum forward voltage@ $I=1.0\text{A}$



Rating and characteristic curves (SL12N THRU SL14N)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

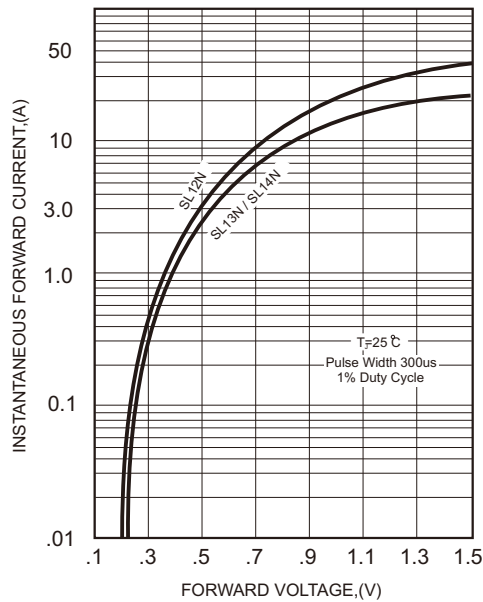


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

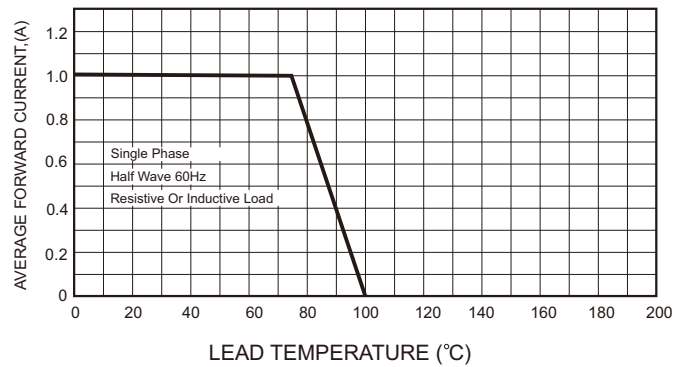


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

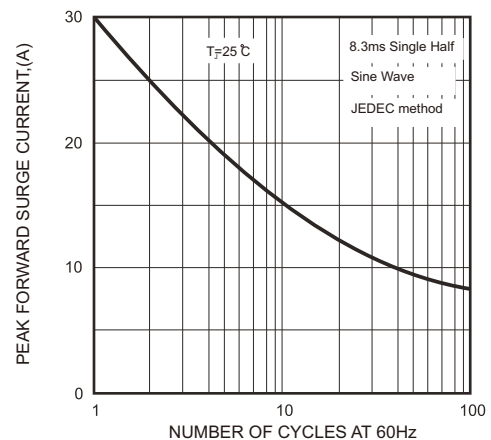


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

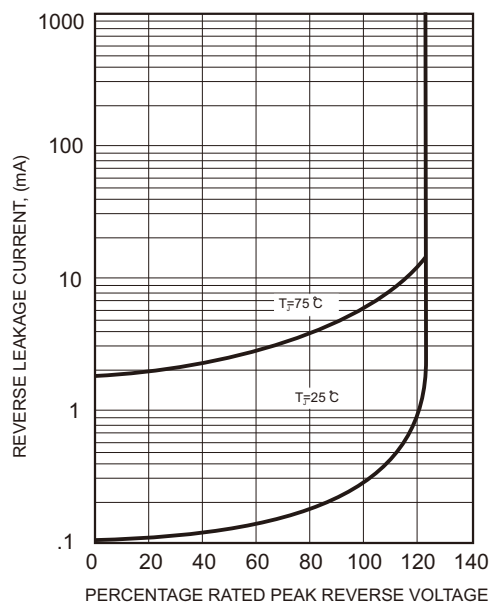
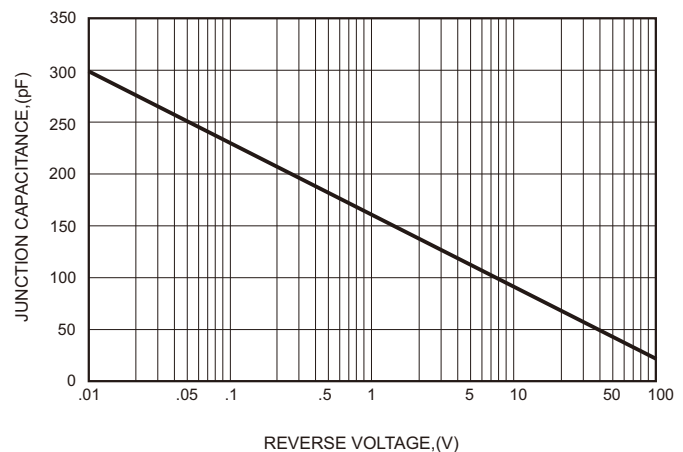


FIG.5-TYPICAL JUNCTION CAPACITANCE





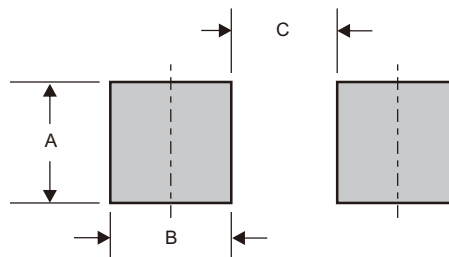
Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Marking

Type number	Marking code
SL12N	L2
SL13N	L3
SL14N	L4

Suggested solder pad layout



Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SOD-323	0.059 (1.50)	0.039 (1.00)	0.051 (1.30)



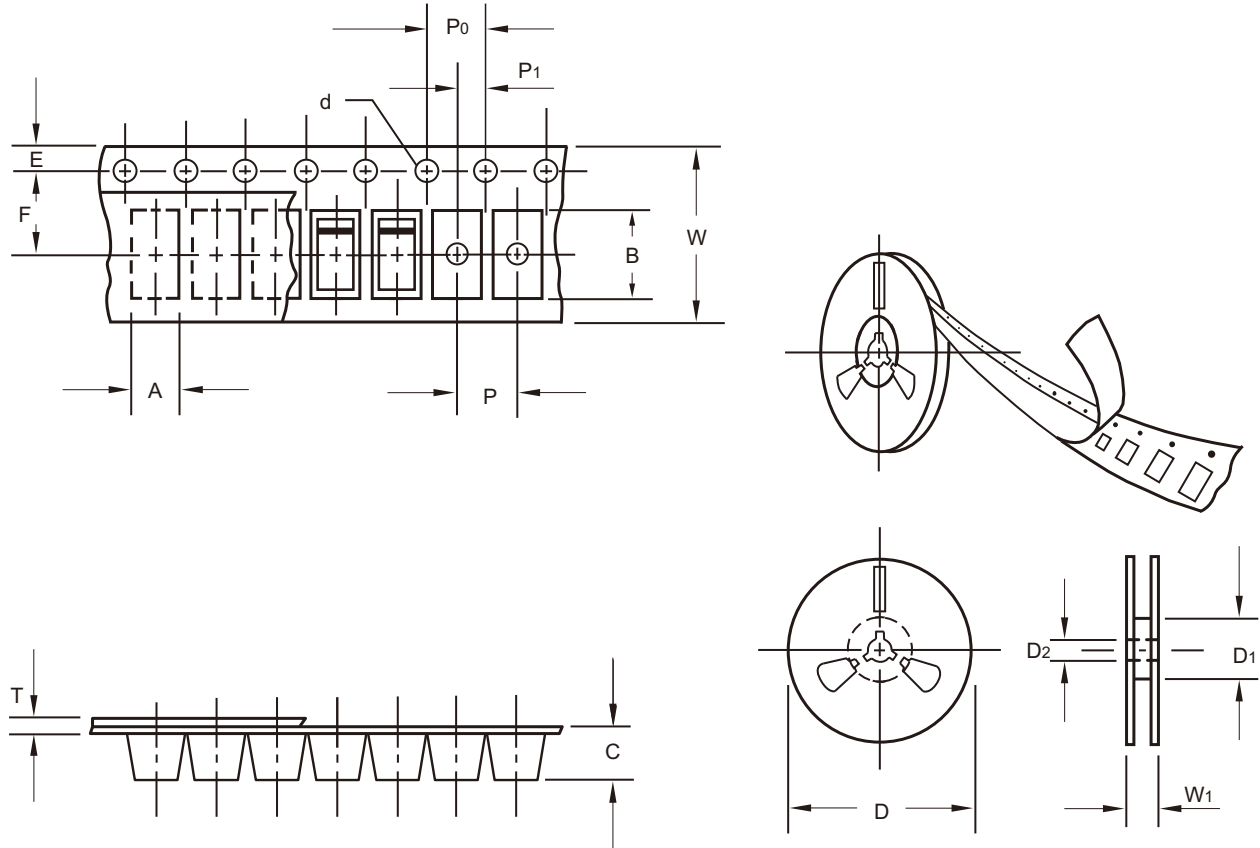
Low VF Chip Schottky Barrier Rectifier

SL12N THRU SL14N

Crownpo Technology

1.0A Surface Mount Schottky Barrier Rectifiers - 20V-40V

Packing information



unit:mm

Item	Symbol	Tolerance	SOD-323
Carrier width	A	0.1	1.47
Carrier length	B	0.1	2.95
Carrier depth	C	0.1	1.15
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	62.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.



Low VF Chip Schottky Barrier Rectifier

SL12N THRU SL14N

Crownpo Technology

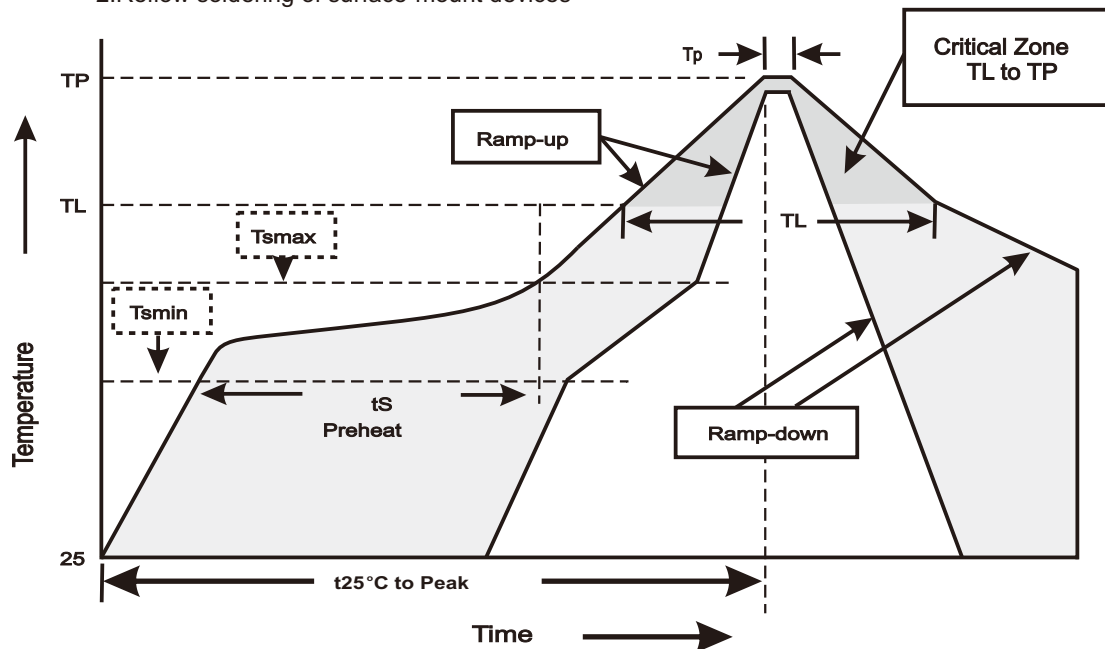
1.0A Surface Mount Schottky Barrier Rectifiers - 20V-40V

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOD-323	7"	3,000	4.0	30,000	183*183*123	178	382*262*387	240,000	8.0

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T _L to T _P)	<3°C/sec
Preheat -Temperature Min(T _{smmin}) -Temperature Max(T _{smmax}) -Time(min to max)(t _s)	150°C 200°C 60~120sec
T _{smmax} to T _L -Ramp-upRate	<3C°/sec
Time maintained above: -Temperature(T _L) -Time(t _L)	217°C 60~260sec
Peak Temperature(T _P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t _P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

*Low VF Chip Schottky Barrier Rectifier***1.0A Surface Mount Schottky Barrier Rectifiers - 20V-40V****High reliability test capabilities**

Item Test	Conditions	Reference
1. Solder Resistance	at $260 \pm 5^{\circ}\text{C}$ for $10 \pm 2\text{sec.}$ immerse body into solder $1/16'' \pm 1/32''$	MIL-STD-750D METHOD-2031
2. Solderability	at $245 \pm 5^{\circ}\text{C}$ for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R = 80\%$ rate at $T_J = 100^{\circ}\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1026
4. Forward Operation Life	Rated average rectifier current at $T_A = 25^{\circ}\text{C}$ for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^{\circ}\text{C}$, $I_F = I_O$ On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	$15P_{SIG}$ at $T_A = 121^{\circ}\text{C}$ for 4 hrs.	JESD22-A102
7. Temperature Cycling	-55°C to $+125^{\circ}\text{C}$ dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Thermal Shock	0°C for 5 min. rise to 100°C for 5 min. total 10 cycles.	MIL-STD-750D METHOD-1056
9. Forward Surge	8.3ms single half sine-wave superimposed on rated load, one surge.	MIL-STD-750D METHOD-4066-2
10. Humidity	at $T_A = 85^{\circ}\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1038
11. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031